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Vishay Siliconix

Automotive N-Channel 150 V (D-S) 175 °C MOSFET

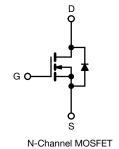


PRODUCT SUMMARY			
V _{DS} (V)	150		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0098		
I _D (A) ^e	98		
Configuration	Single		

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ORDERING INFORMATION	
Package	PowerPAK [®] SO-8L
Lead (Pb)-free and halogen-free	SQJ590EP (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	150	V		
Gate-Source Voltage		V_{GS}	± 20	V		
Continuous Drain Current ^e	T _C = 25 °C ^a	1	98			
	T _C = 125 °C	- I _D	56			
Continuous Source Current (Diode conduction) e		I _S	98	Α		
Pulsed Drain Current b, e		I _{DM}	182			
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	28			
Single Pulse Avalanche Energy	L = 0.1 IIIII	E _{AS}	39	mJ		
Maximum Power Dissipation b, e	T _C = 25 °C	P _D	245	W		
	T _C = 125 °C		81			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C		
Soldering Recommendations (Peak temperature)			260	l		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB mount ^c	R _{thJA}	44	°C/W
Junction-to-Case (Drain) d		R_{thJC}	0.61	C/VV

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 % b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (www.vishay.com/doc?73257).
 d. As per on JESD51-14
- e. Values based on R_{thJC} and T_C of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system.



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		150	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.2	3.0	3.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
Zero Gate Voltage Drain Current		V _{GS} = 0 V	= 0 V V _{DS} = 150 V		-	10	
	I _{DSS}	V _{GS} = 0 V	V _{DS} = 150 V, T _J = 125 °C	-	-	100	μΑ
		$V_{GS} = 0 V$	V _{DS} = 150 V, T _J = 175 °C	-		500	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	10		-	Α
		V _{GS} = 10 V	I _D = 10 A	-	0.0082	0.0098	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	-		0.020	
		V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	-	-	0.028	
Forward Transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		-	70	-	S
Dynamic ^b							
Input Capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	3301	4622	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	1316	1843	
Reverse Transfer Capacitance	C _{rss}			-	25	35	
Total Gate Charge ^c	Q_g		V _{DS} = 75 V, I _D = 25 A	-	34	52	nC
Gate-Source Charge c	Q_{gs}	V _{GS} = 10 V		-	15	-	
Gate-Drain Charge ^c	Q_{gd}			ì	2	-	
Gate Resistance	R_g	f = 1 MHz		0.6	1.5	2.4	Ω
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD} = 75 \text{ V, } R_L = 3 \Omega$ $I_D \cong 25 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1 \Omega$		-	14	21	- ns
Rise Time ^c	t _r			1	19	29	
Turn-Off Delay Time ^c	t _{d(off)}			ı	21	32	
Fall Time ^c	t _f			ı	16	24	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	182	Α
Forward Voltage	V _{SD}	I _F = 10 A, V _{GS} = 0 V		-	0.88	1.2	V
Body diode reverse recovery time	t _{rr}			-	74	148	ns
Body diode reverse recovery charge	Q _{rr}	I _F = 10 A, di/dt = 100A/us		-	240	480	nC
Reverse recovery fall time	ta			-	57	-	ns
Reverse recovery rise time	t _b			-	109	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-7.0	-	А

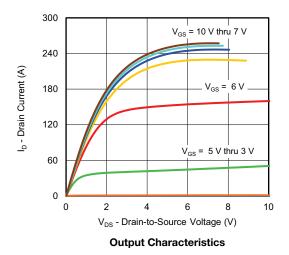
Notes

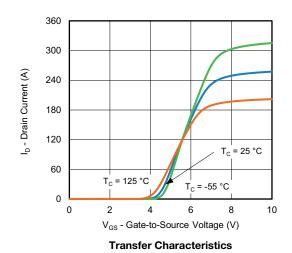
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

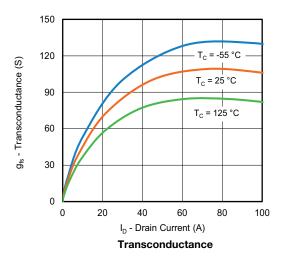
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

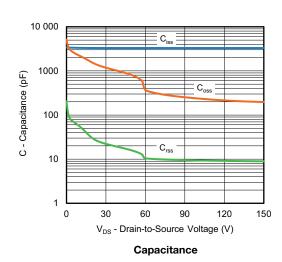


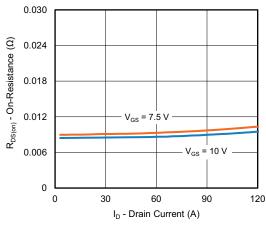
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

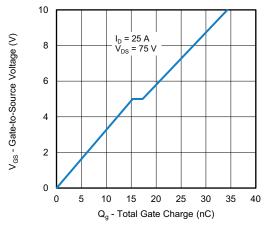








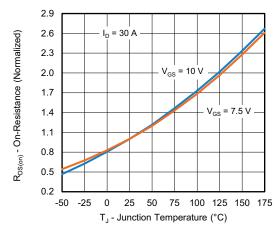




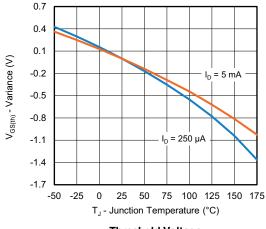
On-Resistance vs. Drain Current



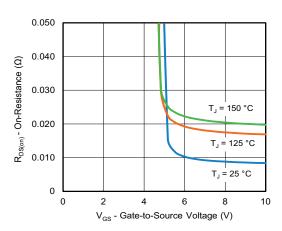
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



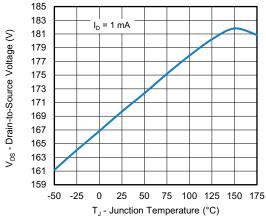
On-Resistance vs. Junction Temperature



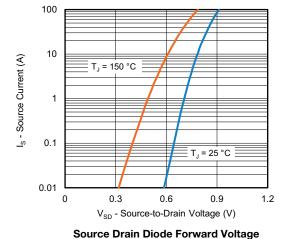
Threshold Voltage

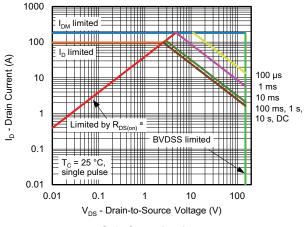


On-Resistance vs. Gate-to-Source Voltage



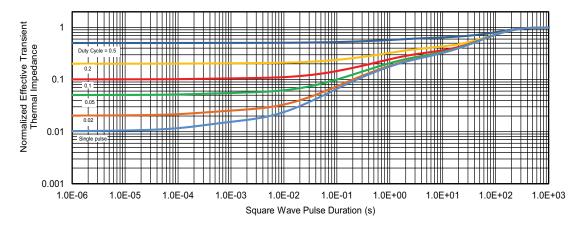
Drain Source Breakdown vs. Junction Temperature



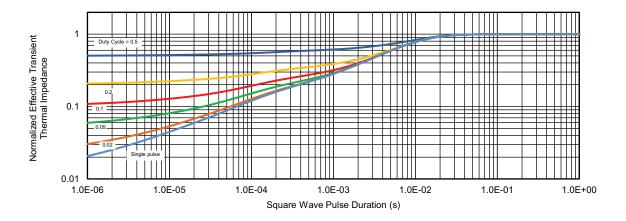


Safe Operating Area

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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